

Supplementary information

A Layered Wide-Gap Oxyhalide Semiconductor with an Infinite ZnO₂ Square Planar Sheet: Sr₂ZnO₂Cl₂

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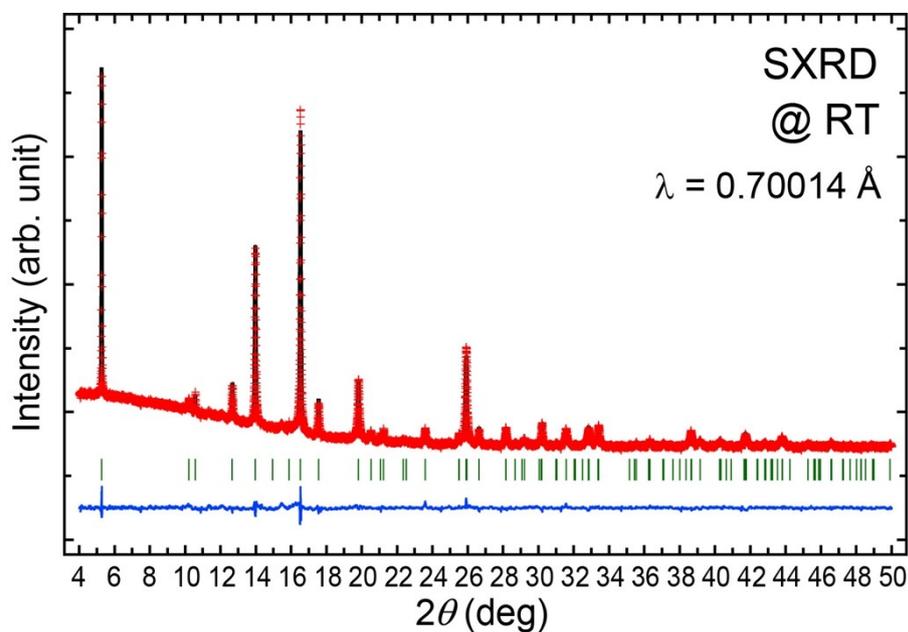


Figure S1. Rietveld structural refinement against the synchrotron diffraction patterns collected from $\text{Sr}_2\text{ZnO}_2\text{Cl}_2$ at room temperature. The zinc oxychloride adopts the $I4/mmm$ space group with $a = 4.06981(2) \text{ \AA}$ and $c = 15.20076(8) \text{ \AA}$. Sr on $4e(0, 0, 0.39328(5))$, Zn on $2a(0, 0, 0)$, O on $4c(0, 0.5, 0)$ and Cl on $4e(0, 0, 0.18260(1))$. No deficiencies were found at all site occupancies. Isotropic atomic displacement parameters (B_{iso}) were $0.252(2) \text{ \AA}^2$ for Sr, $0.25(2) \text{ \AA}^2$ for Zn, $0.8(1) \text{ \AA}^2$ for O and $0.28(5) \text{ \AA}^2$ for Cl. Reliability factors were $R_{\text{wp}} = 1.154\%$ and $R_{\text{B}} = 1.451\%$.

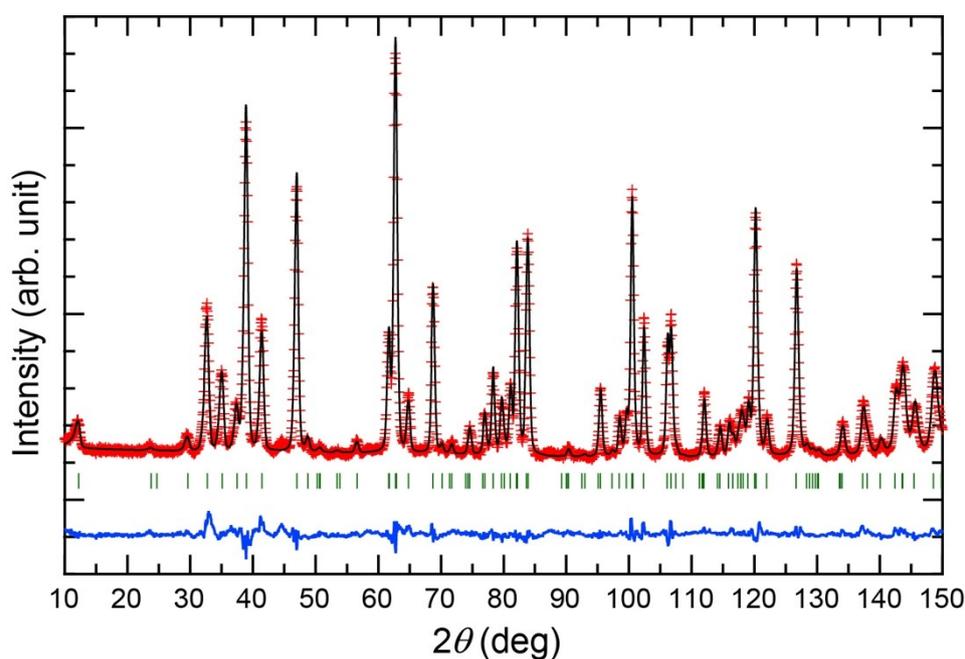


Figure S2. Rietveld structural refinement against the neutron diffraction patterns collected from $\text{Sr}_2\text{ZnO}_2\text{Cl}_2$ at 3 K. The zinc oxychloride adopts the $I4/mmm$ space group with $a = 4.057723(1) \text{ \AA}$ and $c = 15.114116(4) \text{ \AA}$. Sr on $4e$ (0, 0, 0.39208(8)), Zn on $2a$ (0, 0, 0), O on $4c$ (0, 0.5, 0), and Cl on $4e$ (0, 0, 0.18225(7)). The site occupancy factors (g) were fixed at those obtained from the refinements using the 300 K data, namely, $g(\text{Zn}) = 0.962$ and $g(\text{Cl}) = 0.950$. Isotropic atomic displacement parameters (B_{iso}) were $0.204(3) \text{ \AA}^2$ for Sr, $0.03(5) \text{ \AA}^2$ for Zn, $0.408(1) \text{ \AA}^2$ for O, and $0.2150(4) \text{ \AA}^2$ for Cl. Reliability factors were $R_{\text{wp}} = 8.88\%$ and $R_{\text{B}} = 3.83\%$, and Goodness-of-fit = 1.8.

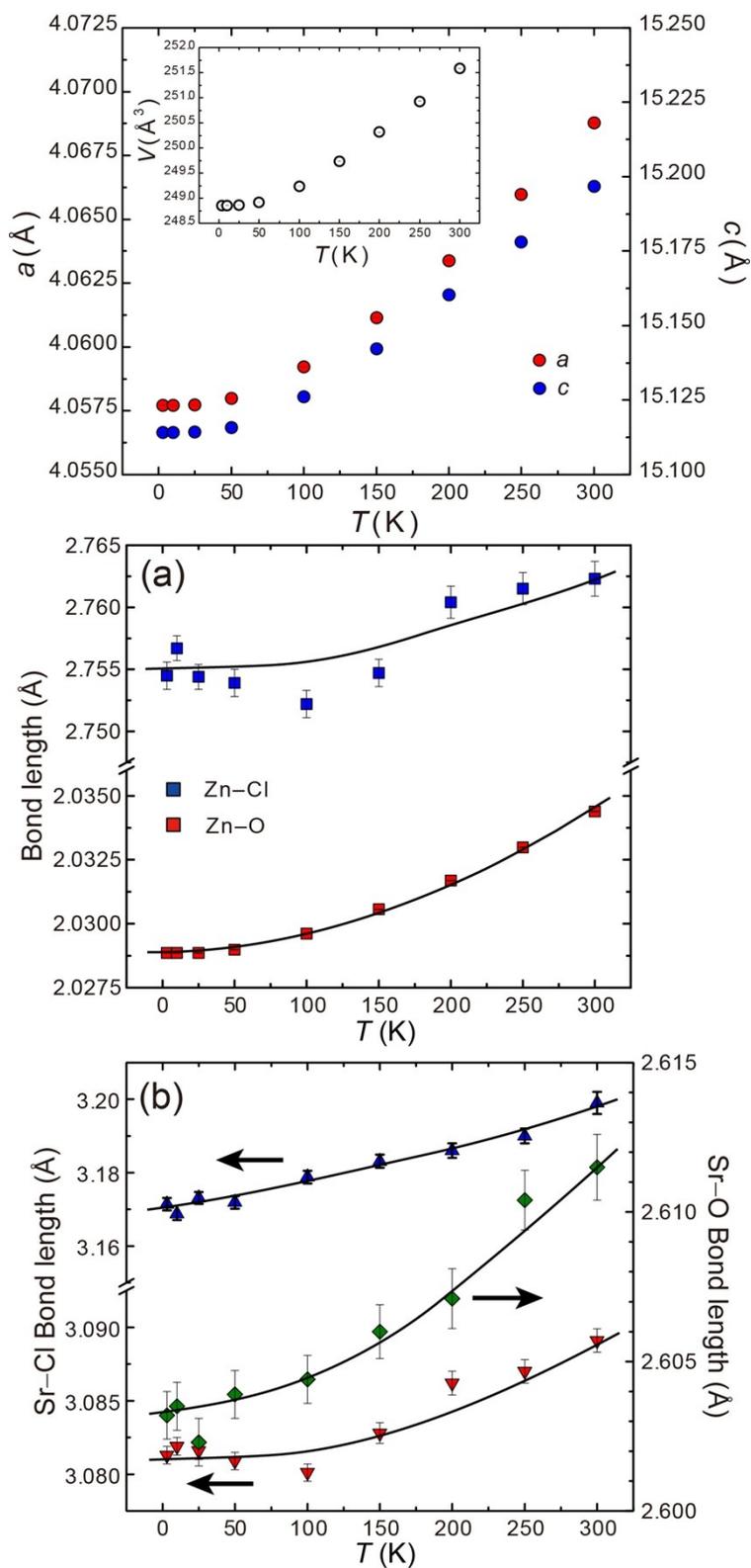


Figure S3. Temperature evolution of the lattice constants, volume, Zn-O/Zn-Cl bond lengths, and Sr-O/Sr-Cl bond lengths, which were obtained by Rietveld structure refinements.

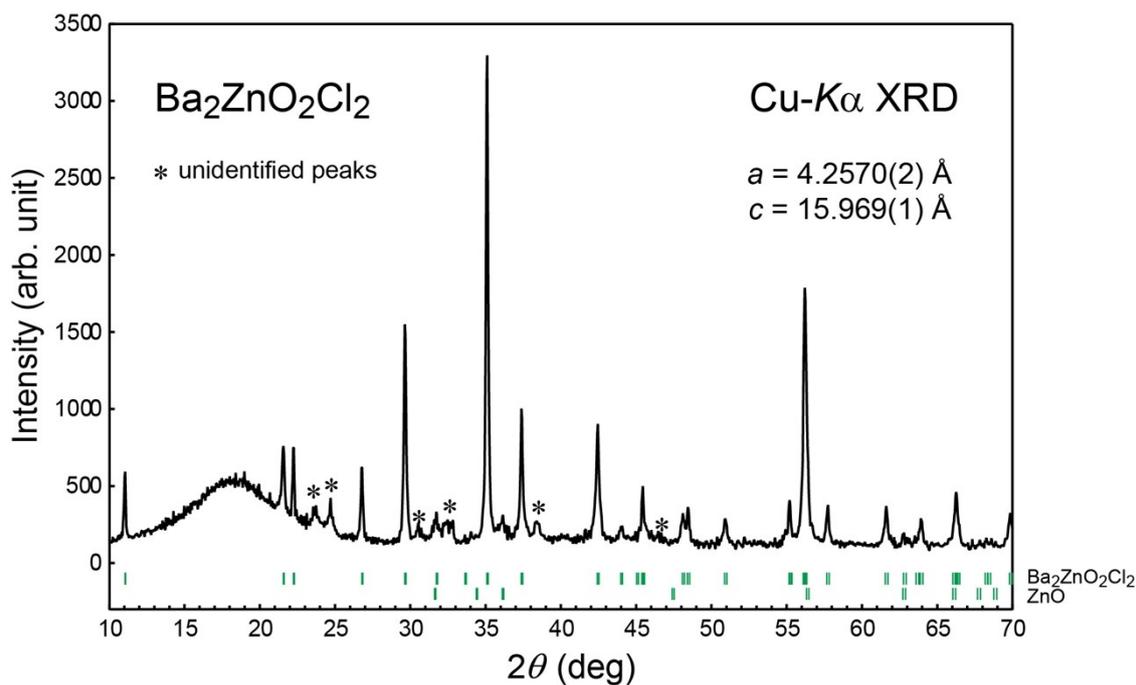


Figure S4. Laboratory X-ray diffraction ($\text{Cu-K}\alpha$ radiation) patterns collected from $\text{Ba}_2\text{ZnO}_2\text{Cl}_2$ at room temperature, which was synthesized at 1800°C and 6 GPa . Due to the hygroscopic nature, the powder sample was suspended in liquid paraffin for the measurement. The XRD data were readily assigned by the $I4/mmm$ space group with $a = 4.2570(2) \text{ \AA}$ and $c = 15.969(1) \text{ \AA}$. In the XRD patterns, wurtzite ZnO and unidentified peaks were detected as impurities. Vertical lines represent expected Bragg peak positions for $\text{Ba}_2\text{ZnO}_2\text{Cl}_2$ ($I4/mmm$) and wurtzite ZnO .

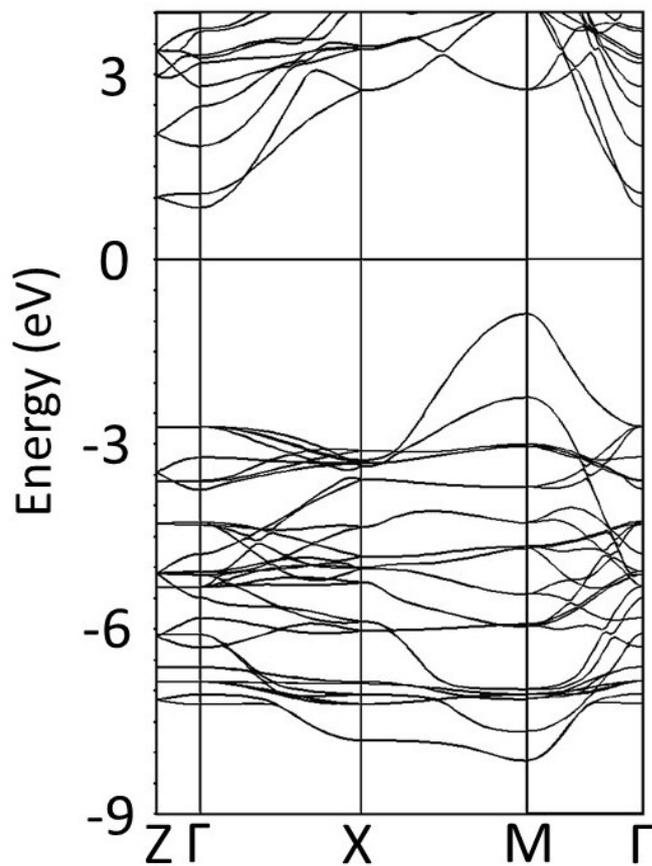


Figure 5. Band dispersions for Sr₂ZnO₂Cl₂ calculated along high symmetry lines within the GGA framework.

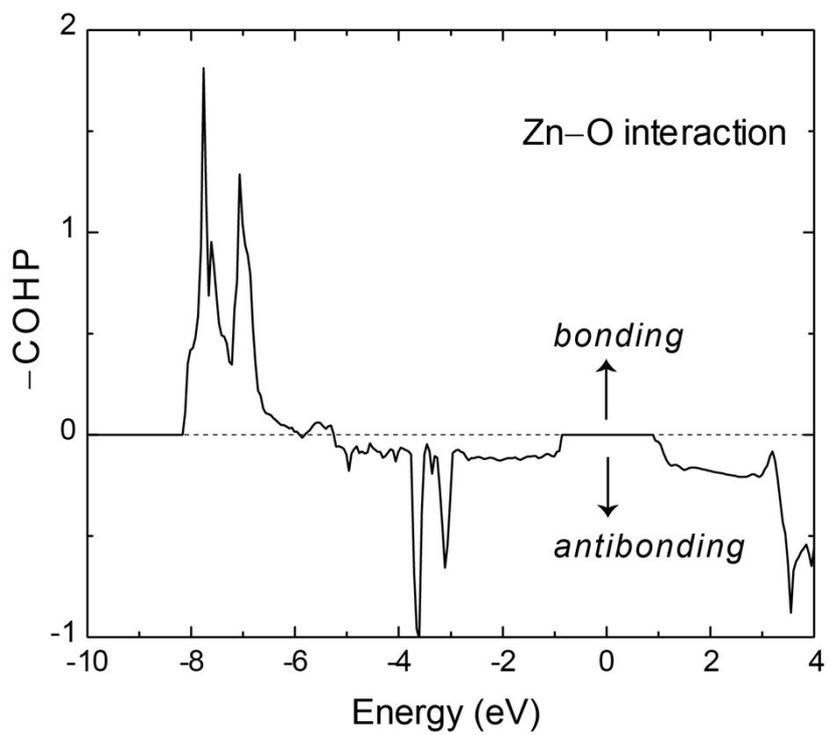


Figure S6. Crystal Orbital Hamiltonian Population (COHP) for Zn-O interaction in $\text{Sr}_2\text{ZnO}_2\text{Cl}_2$. The COHP curve shows bonding state between Zn $3d$ and O $2p$ orbitals in the energy range from -8 to -6 eV, but antibonding states in the valence band maximum.